

# SILICON EPITAXIAL HIGH SPEED SWITCHING DIODE

#### **Features**

- · Smal plastic package suitable for surface mounted
- High Speed (Trr = 1.2 ns Typ.)
- · High reliability with high surge current handling capability
- · RoHS compliant package

#### **Applications**

· High speed switching

#### **Description**

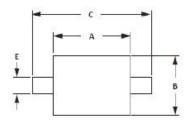
· Silicon planar zener diode in a small plastic SMD SOD-323 package

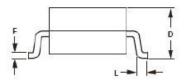
#### **Packing & Order Information**

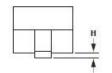
3,000/Reel











OUTLINE DIMENSIONS								
DIM	MILLIMETERS		INCHES					
	MIN	MAX	MIN	MAX				
Α	1.60	1.90	0.063	0.075				
В	1.15	1.45	0.045	0.057				
С	2.39	2.70	0.094	0.106				
D	0.80	1.10	0.031	0.043				
Е	0.25	0.40	0.010	0.016				
F	0.10	0.20	0.004	0.008				
Н	-	0.10	-	0.004				
L	0.20	-	0.008	-				

- Controlling dimension: millimeters.
   Dimensioning and tolerances per ANSI Y14.5M, 1985.
   Dimensions are exclusive of mold flash and metal burrs.

### **Graphic symbol**



#### MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Maximum Ratings and Thermal Characteristics (Rating at 25 °C ambient temperature unless otherwise specified.)									
Parameter	Symbol	Value	Unit						
Maximum Peak Reverse Voltage	VRRM	90	V						
Maximum DC Reverse Voltage	VRM	80	V						
Maximum Average Forward Current	IF	100	mA						
Maximum Peak Forward Voltage	IFM	255	mA						
Maximum Surge Current (1s)	IFSM	500	mA						
Maximum Junction Temperature	TJ	125	°C						
Storage temperature range	TS	-55 to +175	°C						



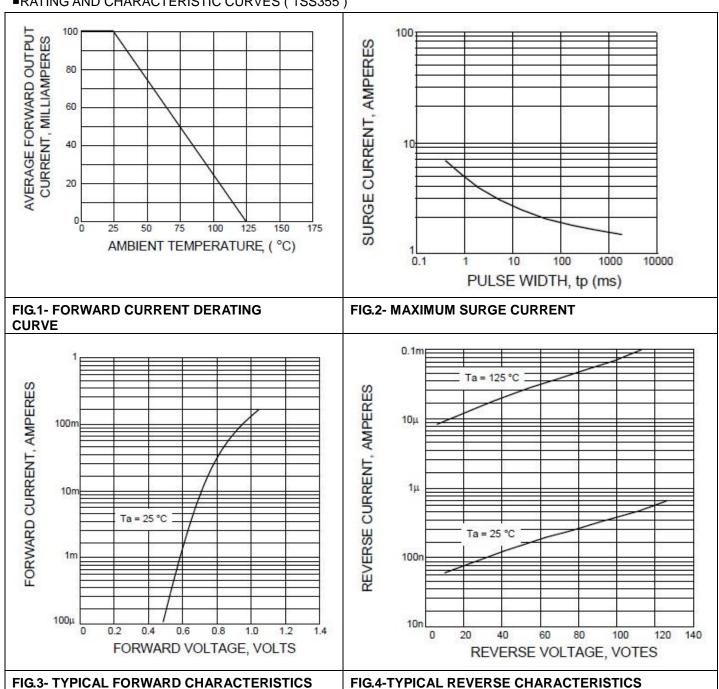
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Electrical characteristics (Tc=25°C unless otherwise noted)										
Parameter	Test Condition	Symbol	Min.	Тур.	Max.	Unit				
Forward Voltage	I <sub>F</sub> = 100 mA	VF			1.2	V				
Reverse Current	V <sub>R</sub> = 80 V	IR			0.1	μA				
Capacitance between terminals	f = 1MHz ; V <sub>R</sub> = 0.5	СТ			3.0	pF				
Davara Dasavar Tima	$I_F = 10 \text{ mA}$ , $V_R = 6 \text{ V}$	Tee			4.0	ns				
Reverse Recovery Time	R <sub>L</sub> = 100 Ω	Trr								



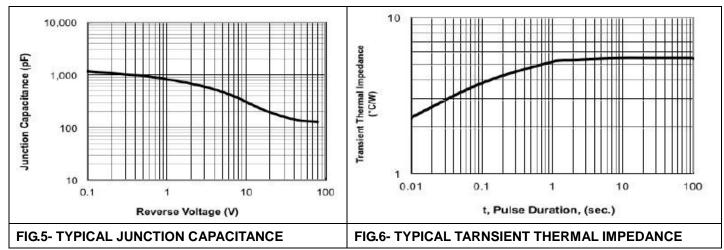
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■RATING AND CHARACTERISTIC CURVES (1SS355)





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